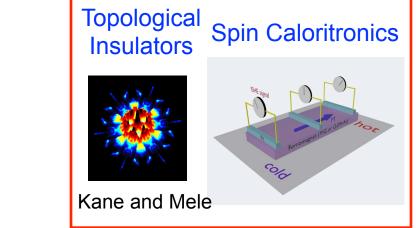
## Theory Panel 2: (2<sup>nd</sup> Principles, mixed bag)

•(Sinova) Topological thermoelectrics and a mixed bag of questions



•(Onoda) Thermoelectric and transport properties of gapped TI coupled to magnetic systems

#### (-20 minutes)

(2 hours)

•(Xie) Spin superconductor in ferromagnetic graphene (-20 minutes)

# •(Lee) Magnetization dynamics coupled with spin and spin waves

(-20 minutes)



Key discussion during the workshop: what to call the field Heattronics? Thermomagnotronics? Nanospinheat ? Calefactronics? Fierytronics? Coolspintronics? Thermospintronics?

What I learned in kinder garden: Fire is cool

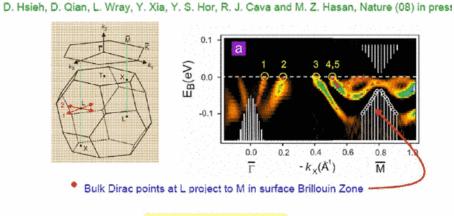


What I learned in Leiden: Spin+Fire is cooler



### **3D Topological Band Insulators**

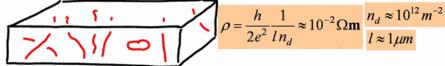
Experimental Candidate Bi<sub>0.9</sub>Sb<sub>0.1</sub>



$$v_0 = 1; \mathbf{M}_v = (1,1,1)$$

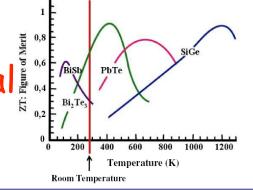
#### **Experimental Signatures**

 Resistivity: dislocation contribution could dominate over surface conduction.



 Scanning Tunneling Microscopy: Can determine atomic defect structure and Local Density of States (LDOS). 1D modes – finite DOS. Dirac point – vanishing density of states.

High ZT is related to topological protected states



University of Hamburg

BMBF Nanofutur Group

 $\mu \Phi$ 

MPI-MSP Halle

Prediction: ZT will be MUCH larger in HgTe wells in the inverted regime and in thin ribbon 3D TI through 1D channels

The Important Thermoelectric Materials

## **Topological thermoelectrics**



JAIRO SINOVA Texas A&M University Institute of Physics ASCR



### Open postdoc position (free stakes; summers in Prague; winters in Texas; cowboy hat; free rodeo classes)

Oleg Tretiakov, Artem Abanov, Suichi Murakami

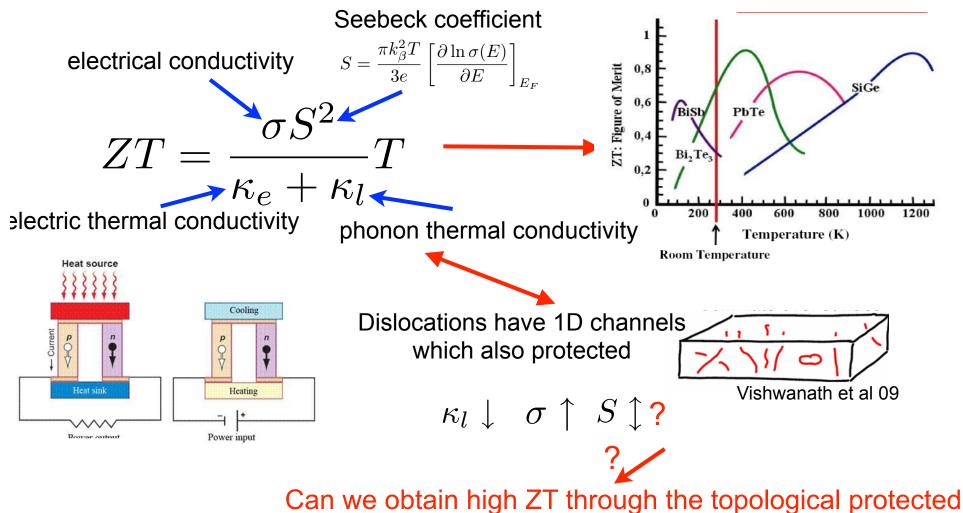
Research fueled by:







#### From topological insulators to thermoelectrics



states; are they related to the high ZT of these materials?

## Possible large ZT through dislocation engineering

APPLIED PHYSICS LETTERS 97, 073108 (2010)

#### Large thermoelectric figure of merit for three-dimensional topological Anderson insulators via line dislocation engineering

O. A. Tretiakov, Ar. Abanov, Shuichi Murakami, and Jairo Sinova<sup>1</sup> (Received 23 July 2010; accepted 30 July 2010; published online 18 August 2010)

$$\frac{1}{ZT} = \frac{(L_0^b + snL_0^{1D})(L_2^b + snL_2^{1D} + \kappa_{ph}T)}{(L_1^b + snL_1^{1D})^2} - 1$$

 $Bi_{1-x}Sb_x$  (0.07 < x < 0.22)

(a) E

where the L's are the linear Onsager dynamic coefficients

$$L^{1D}_{\alpha} = -\frac{l}{sh} \int \mathcal{T}(E) f'(E) (E - \mu)^{\alpha} dE$$

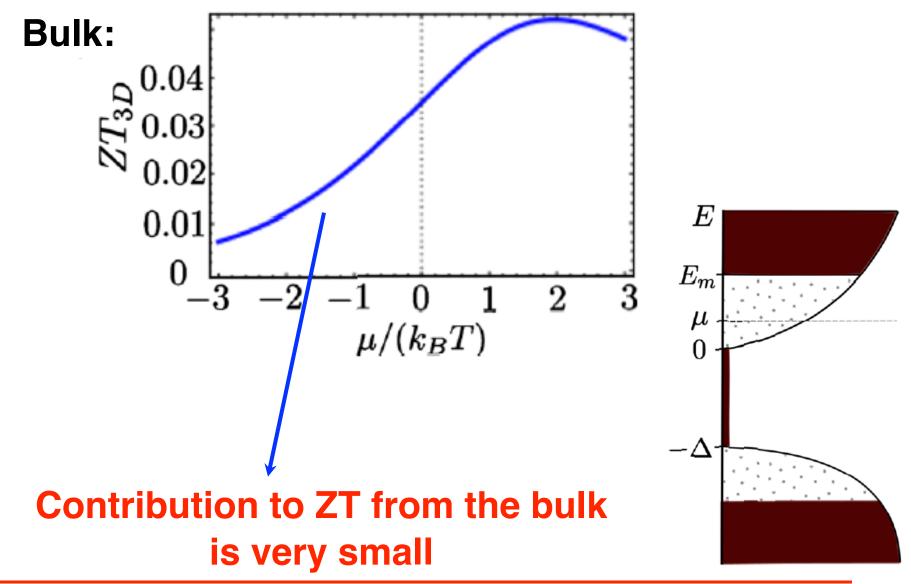
$$L^{b}_{\alpha} = -\tau \int_{E_{m}}^{\infty} D(E) f'(E) v^{2} (E - \mu)^{\alpha} dE$$

$$Localized bulk states$$

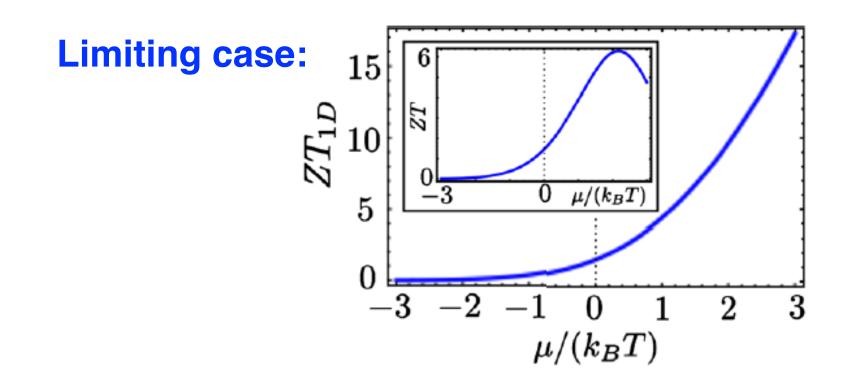
$$L^{b}_{\alpha} = \frac{2\sqrt{2m^{*}}}{\pi^{2}\hbar^{3}} \tau cT^{\alpha+3/2} \int_{\frac{E_{m}-\mu}{T}}^{\infty} dx \frac{x^{\alpha} (x + \mu/T)^{3/2} e^{x}}{(e^{x} + 1)^{2}}$$
The tick we have been of the part of

Tretiakov, Abanov, Murakami, Sinova APL 2010

## **Bulk contribution**



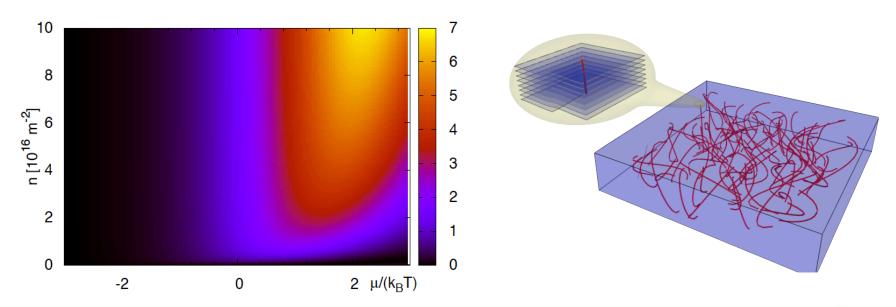
#### ZT of one perfectly conducting 1D wire



infinite density of dislocations

$$ZT_{1D} = \lim_{n \to \infty} ZT = \frac{(L_1^{1D})^2}{L_0^{1D} L_2^{1D} - (L_1^{1D})^2}$$

## Possible large ZT through dislocation engineering

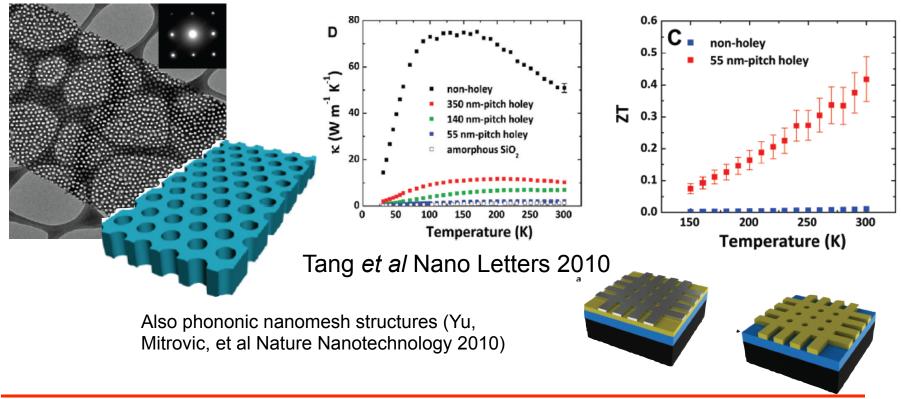


Remains <u>very</u> speculative but simple theory gives large ZT for reasonable parameters

Tretiakov, Abanov, Murakami, Sinova APL 2010



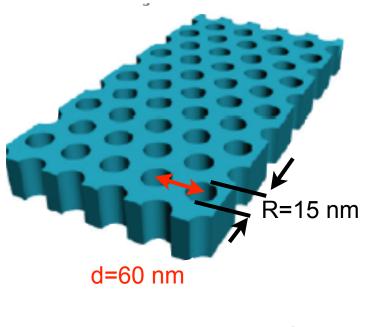
So far only one material is believed to have protected 1D states on dislocations: how to further exploit TI properties to increase ZT? Analogy to HolEy Silicon



Extending the idea to the entire class of TI insulators

$$\frac{1}{ZT} = \frac{(L_0^b + NL_0^s)(L_2^b + NL_2^s + (\kappa_{ph} + N\kappa_{ph}^s)T)}{(L_1^b + NL_1^s)^2} - 1$$

$$L_{\alpha} = L_{\alpha}^{b} + NL_{\alpha}^{s}$$

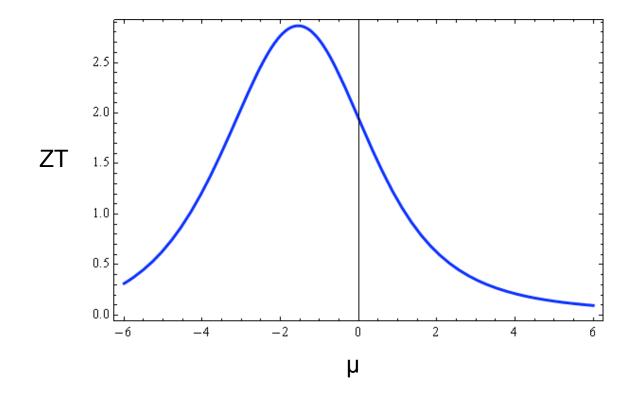


$$\kappa_{ph} \approx 0.01 \mathrm{Wm}^{-1} \mathrm{K}^{-1}$$

$$ZT_{2D} = \lim_{n \to \infty} ZT = \frac{(L_1^s)^2}{L_0^s (L_2^s + \kappa_{ph}^s T) - (L_1^s)^2}$$

Tretiakov, Abanov, Sinova (in preparation) 2011

Preliminary results (week ago)



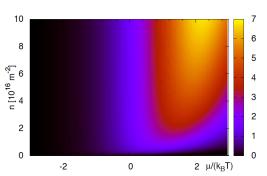
Summary of topological thermoelectrics

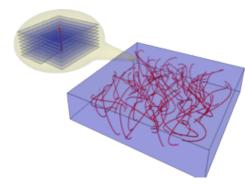
•Qualitative theory was developed on how to increase *ZT* in topological insulators via line dislocations.

•The interplay of topologically protected transport through the dislocations and Anderson insulator in the bulk.

•Estimated  $ZT \sim 10$  at room temperature.

•Idea can be extended to the entire range of TI

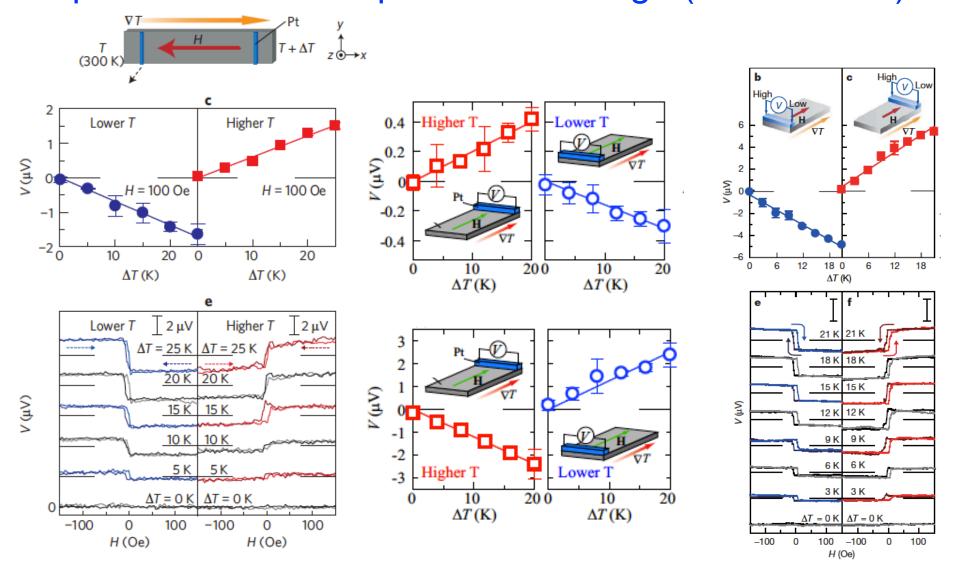




#### NOW SOME RANDOM THOUGHTS FROM THIS WEEK: DISCUSSION TIME

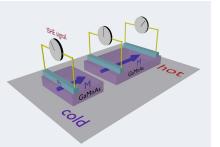
## Which one is which?

Spin Seebeck? or Spin ....something? (Ron Jansen)



•More experiments in more materials (Spin Seebeck)

- •Several teams see the same effect.
- •Phonon's on the substrate playing a key role
- •Sign changes with different materials



- •Experiments are a bit too complicated (too many competing thing; sometime more does not lead to better understanding)
- Theory of Spin Seebeck (an evolution): some progress and some difficulties
  There seems to be agreement on the mechanism that injects the spincurrent (spin-pumping); is it the only one possibility?
  Different scenarios that create the non-equilibrium condition for finite spin pumping (magnon-phono drag, Sanders-Walton)
  SIGN PROBLEM: if correct the theory has problems
- Magnetic heat engines: a clear definition of ZT in magnetic systems
   AGAIN: is there a ZT (e.g. can one create a heat engine) from spin Seebeck?

Checks (Japan Group)	Checks (OSU Group)
Spin Seebeck measured in different	•Bilayer system: WHY additive; why GaMnAs
materials: Ni (opposite sign) and Fe	overwhelms MnAs? Obviously exchange bias
BUT ISHE FMR measurement gives same	plays a role but how? Shouldn't the focus be
sign!!!	to simplify (YT)
Did not try non-ferromagnetic metals	•GaMnAs (Magnetic Semiconductor) measured as
No V(ISHE) signal seen when:	a function of T
• Permalloy without Pt bar contacts	•Measured paramagnetic sample with Pt contacts
• When whole sample is made of Pt	= 0 signal
• Permalloy with Cu leads	•Did measurements to try to exclude the Planar
• If ΔT = 0	Nernst contributions
<ul> <li>If ∆T = 0</li> <li>In YIG, SiO<sub>2</sub> between the Pt (this check is</li> </ul>	<ul> <li>Measured transverse V w/ Pt point contacts, one observes Nernst contribution and ISHE (Nernst</li> </ul>

 Measured transverse V w/ Pt point contacts, one observes Nernst contribution and ISHE (Nernst overpowers?)

Wish lists of Checks (To do)

•Kerr Microscopy??

not done in FeNi)

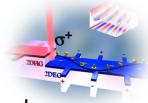
- Measure regular Seebeck in cut samples (as a thermometer)
- Different widths of Pt and sample
- •Instead of cut, remove the sapphire and leave a slip (done)
- Metal with Pt strip (check missing from Japanese group) (done?)
- •Heat pulse experiments (heat solitons) form DC to AC
- •Separate contacts on edges of sample and Pt strip (measure a vertical voltage?)
- How does signal depend on geometry of Pt (ex. bigger depth leading to shorting)

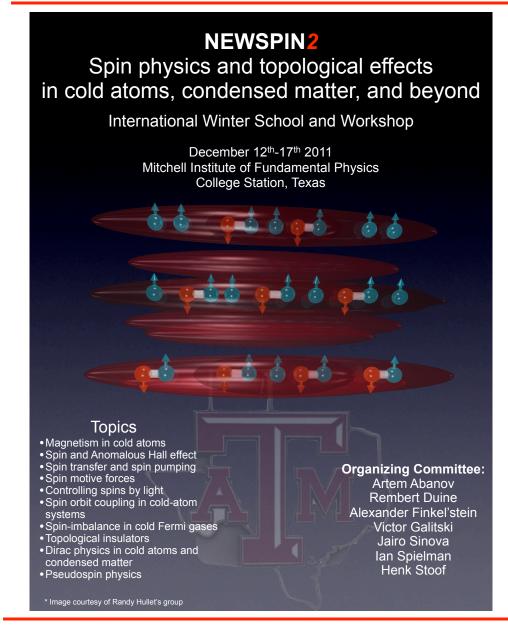


## BUT it takes MANY to do the spin caloritronics tango!!



## Spin in Cold Atoms and CM systems





3 day Winter School and 3 day Workshop http://newspin2.physics.tamu.edu/





Nanoelectronics, spintronics, and materials control by spin-orbit coupling